

DETAILED ACTION

1. In accordance with 37 CFR 1.175(b)(1), a supplemental reissue oath/declaration under 37 CFR 1.175(b)(1) must be received before this reissue application can be allowed.

Claims 1-22 are rejected under 35 U.S.C. 251 as being based upon a defective reissue declaration. See 37 CFR 1.175.

At least in the 08/11/2009 supplemental amendment, claims 1-22 have been further corrected for "errors" under 35 U.S.C. 251. However, such corrected "errors" under 35 U.S.C. 251 have not been identified in the original filed reissue oath/declaration and/or in any other oaths/declarations filed so far.

Receipt of an appropriate supplemental oath/declaration under 37 CFR 1.175(b)(1) will overcome this rejection under 35 U.S.C. 251. An example of acceptable language to be used in the supplemental oath/declaration is as follows:

"Every error in the patent which was corrected in the present reissue application, and is not covered by a prior oath/declaration submitted in this application, arose without any deceptive intention on the part of the applicant."

Note: If additional defects or errors are corrected in the reissue after the filing of the application and the original reissue oath or declaration, a supplemental reissue oath/declaration must be filed, unless all additional errors corrected are spelling, grammar, typographical, editorial or clerical errors which are not errors under 35 U.S.C. 251 (see MPEP §1402). In other words, a supplemental oath/declaration is required where any "error" under 35 U.S.C. 251 has been corrected and the error was not identified in the original reissue oath/declaration. See MPEP 1414.01.

Therefore, a Supplemental Reissue Declaration is required for the corrections/amendments to the claims which were filed on 4/16/08 and thereafter.

Claim Objections

Claims 3 and 12 are objected to because of the following informalities and/or defects:

In claim 3, line 5, the term of "said second gate" should read as: -- said second gate electrode --.

In claim 12, line 8, the term of "in a first doping state in a form of" should read as: -- in the first doping state in a form of --.

In claim 12, line 15, the phrase of ", at least every of first gates being formed in the gate forming region" should be deleted.

Appropriate correction is required. (Based on the 08/11/2009 supplemental amendment. Please keep the same format, i.e., one marked version showing the net changes from the patent, and another marked version showing the changes from the previous amendment)

Allowable Subject Matter

2. Claims 1-22 would be allowable if rewritten or amended to overcome the rejection(s) under 35 U.S.C. 251 and the claim objections set forth in this Office action.

Reasons For The Indication Of Allowable Subject Matter

3. The following is a statement of reasons for the indication of allowable subject matter:

The prior art does not teach or render obvious of a semiconductor device as defined in the above claims, comprising particularly:

a first main electrode formed over an interlayer insulating film on a first gate electrode, the first main electrode covering and electrically connected a surface of a second semiconductor region and having an end extending to a boundary between the peripheral portion of a first major surface of the substrate and the central portion of the first major surface; and, an integral semi-insulating plasma CVD nitride film covering at least the peripheral portion but not the central portion and not extending above any gate electrode, wherein the integral semi-insulating plasma CVD nitride film has a conductivity which does not lose function as an insulating film and stabilizes breakdown voltage characteristics of the semiconductor device.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shouxiang Hu whose telephone number is 571-272-

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1654. The examiner can normally be reached on Monday through Friday, 8:30 AM to 5:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Lynne Gurley can be reached on 571-272-1670. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Shouxiang Hu/
Primary Examiner, Art Unit 2811